

REMARKS

Claims 1-7 are pending in this application. By this Amendment, claims 1-3 are amended to better distinguish over the applied references. Reconsideration in view of the above amendments and following Remarks is respectfully requested.

Entry of the amendments is proper under 37 C.F.R. §1.116 since the amendments: (a) place the application in condition for allowance (for the reasons discussed herein); (b) do not raise any new issue requiring further search and/or consideration (since the amendments amplify issues previously discussed throughout prosecution); (c) satisfy a requirement of form asserted in the previous Office Action; (d) do not present any additional claims without canceling a corresponding number of finally rejected claims; and (e) place the application in better form for appeal, should an appeal be necessary. The amendments are necessary and were not earlier presented because they are made in response to arguments raised in the final rejection. Entry of the amendments is thus respectfully requested.

The Office Action rejects claims 3 and 4 under 35 U.S.C. §112, second paragraph. Claim 3 is amended to obviate the rejection. Thus, it is respectfully requested that the rejection be withdrawn.

The Office Action rejects claims 1-3 and 5 under 35 U.S.C. §103(a) as being unpatentable over Cherne (U.S. Statutory Invention Registration H1435) in view of Hisamoto (U.S. Patent No. 5,115,289); and claims 6 and 7 are rejected under 35 U.S.C. §103(a) as being unpatentable over Cherne in view of Hisamoto and Yamazaki (U.S. Patent No. 5,959,313). The rejections are respectfully traversed.

In particular neither Cherne, Hisamoto nor Yamazaki, either alone or in combination, disclose or suggest a thin film transistor, including at least an extension of a gate electrode extending outwardly above and outside of a channel region, as recited in independent claim 1.

Furthermore, neither Cherne, Hisamoto nor Yamazaki, either alone or in combination, disclose or suggest a thin film transistor, including at least extensions extending from both ends of a gate electrode outside of the channel region and along a channel longitudinal direction, as recited in independent claim 2.

Specifically, Cherne discloses in Figures 11 and 12 that the gate structure is positioned directly above the body/channel region. Thus, no part of the gate structure extends outside of the body/channel region.

Hisamoto discloses in Figures 2c and 2d source wiring 40' and a polycrystalline silicon layer 30' which become the gate electrode.

Yamazaki discloses using thin film transistors in a display device as a driving circuit and using that display device in an electronic apparatus.

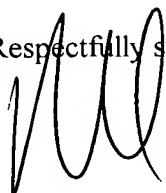
In contrast to the claimed invention, neither Cherne, Hisamoto nor Yamazaki, disclose or suggest a thin film transistor, including at least an extension of the gate electrode extending outwardly above and outside the channel region. Furthermore, none of the applied references disclose or suggest at least extensions extending from both ends of the gate electrode outside of the channel region analogue a channel longitudinal direction. On the contrary, nowhere in the applied references is it disclosed or suggested that the gate extends outside the body/channel region.

Thus, the applied references would not have resulted in enlarging a side area of the gate electrode in order to improve a heat radiation efficiency of the TFT. Because any combination of the applied references would not have resulted in the thin film transistor of claims 1-7, it would not have been obvious to combine the applied references to arrive at the claimed invention. Accordingly, it is respectfully requested that the rejections under 35 U.S.C. §103(a) be withdrawn.

In view of the foregoing, this application is in condition for allowance. Favorable reconsideration and prompt allowance of claims 1-7 are earnestly solicited.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number set forth below.

Respectfully submitted,



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